

**AMENDMENTS TO THE ABSTRACT**

Please substitute the following paragraphs for the abstract now appearing in the currently filed specification:

A simple method is provided for obtaining a bipolar transistor being free of current gain dispersion and having a lowered base resistance.

The method of the present invention comprises forming a base layer on a semiconductor substrate, then forming in an insulating film stacked on the base layer a base electrode lead opening and an emitter electrode lead opening at the same time, and subsequently forming a base electrode lead portion and an emitter electrode lead portion in, respectively, the base electrode lead opening and the emitter electrode lead opening.